B. ETCE 4TH YEAR 1ST SEMESTER EXAMINATION, 2018 MICROWAVE ENGINEERING

Time: 3 Hours

Full Marks: 100

Use separate Answer - Script for each Part 50 marks for each part

B) A three port circulator has an insertion loss of 1 dB, isolation 30 dB and VSWR 1.5. Find the S-matrix. [8] C) Find the resonant frequencies of the five lowest modes of an air-filled cylindrical cavity of radius 1.905 cm and length 2.54 cm. list them in assending order. [5] D) Determine the length of a cavity which will resonate at 10 GHz. The cavity is made from WG 16 of the shortest length, calculate Q-factor. [3+4]4. A) What do you meant by waveguide discontinuity? How this discontinuity related with the change of height and width of waveguide? [2+5]B) Give the equivalent transmission line representation for TE mode. [5] C) Briefly explain the function of waveguide bends and twists. [5] E) Mention the areas of application of Magic-T. [4] F) Give the impedance versus frequency curve of a parallel resonant RLC circuit and define bandwidth. [4]

Ref. No.: Ex/ET/T/414/2018

B.E. ELECTRONICS AND TELE-COMMUNICATION ENGINEERING FOURTH YEAR, FIRST SEMESTER EXAM 2018

MICROWAVE ENGINEERING

Time (Full Paper): Three hours

Full Marks of (Part II): 50

Use separate answer scripts for each half.

PART II

Answer **Q.1** and *any two* questions from the rest. Use separate Smith charts for individual questions if required.

- a) Explain TDR. What type of measurements can be carried out using TDR? [3+2]
 b) Discuss on different microwave power detectors and compare their performances along with suitable applications. [5]
 c) Explain high VSWR (>10) measurement technique. [4]
- 2. a) "Another limitation in application of conventional tubes at microwave frequencies is the electron transit angle between electrodes." explain. Explain other limitations using proper arguments. [3+6]
 - b) With examples explain "Reentrant Cavities". Draw a neat diagram of a coaxial cavity and find its resonant frequency. [3+6]
- 3. a) Draw a neat diagram of two cavity klystron amplifier. Explain velocity modulation and derive the equation for velocity modulation. Explain beam coupling coefficient and depth of modulation. [10]
 - b) A two cavity klystron has Vo = 1000V. Find the electron velocity leaving the cathode. If the beam coupling coefficient is 0.95 then find the gap transit angle. You may state all assumptions required to obtain a solution. [8]
- 4. a) Why high frequency transistors are characterized by S-parameters? Why cannot S_{12} for a transistor be equal to S_{21} ? [3+3]
 - b) How will you represent a BJT amplifier as two port network? Draw a two-port transistor amplifier network with general source and load impedances and define source, load, input and output reflection coefficients ($\Gamma_{\rm S}$, $\Gamma_{\rm L}$, $\Gamma_{\rm in}$ and $\Gamma_{\rm out}$). Calculate the power gain, available gain, the transducer power gain, and the unilateral transducer power gain of this amplifier in terms of transistor S-parameters and different reflection coefficients. [12]
- 5. a) Why do you need to test the stability of an amplifier? What are the differences between conditional and unconditional stability? Derive the equations for stability circles. [2+2+8]
 - b) An amplifier uses a transistor with the following s-parameters at 2 GHz ($Z_0 = 50$ Ohm):

 $S_{11} = 0.894 \angle -60.6^{\circ}$, $S_{21} = 3.122 \angle 123.6^{\circ}$, $S_{12} = 0.02 \angle 62.4^{\circ}$, $S_{22} = 0.781 \angle -27.6^{\circ}$. Determine its stability and plot stability circle on smith chart. Explain your plots. [6]

6. Write short notes on (Any three):

 $[3 \times 6 = 18]$

- a) Microwave power measurement techniques
- b) Spectrum Analyzer
- c) Reflex klystron
- d) PIN diode based microwave switches